

FIG.2

PLASMA SOURCE POWER	1000W
NH ₃ FLOW RATE	125ml/min
PROCESSING PRESSURE	0.5Pa
WAFER SUBSTRATE TEMPERATURE	20°C
POWER APPLIED TO SUBSTRATE	850W(8-INCH WAFER)

FIG.3

PLASMA SOURCE POWER	1000W
NH₃ FLOW RATE	125ml/min
CO FLOW RATE	50ml/min
PROCESSING PRESSURE	0.7Pa
WAFER SUBSTRATE TEMPERATURE	20°C
POWER APPLIED TO SUBSTRATE	850W(8-INCH WAFER)

FIG.4

PLASMA SOURCE POWER	1000W
NH₃ FLOW RATE	125ml/min
Ar+CH ₄ FLOW RATE	375ml/min
PROCESSING PRESSURE	2.0Pa
WAFER SUBSTRATE TEMPERATURE	20°C
POWER APPLIED TO SUBSTRATE	850W(8-INCH WAFER)

FIG.5

	PRIOR ART	PRESENT INVENTION
ORGANIC FILM		
ETCHING RATE	488(nm/min)	405(nm/min)
SELECTIVE		
RATIO TO HM	44(—)	59(—)
NUMBER OF		
CONTAMINANTS		
OVER 0.20 µm	224	25
RESIDUALS	HM RESIDUALS	HM NO RESIDUALS
		ORGANIC FII M
-	URGAINIC FILIN	

AMOUNT OF RESIDUALS CRITERIA OF CONTROL OF RESIDUALS

HIGH

DIELECTRIC CONSTANT